

**isc Silicon NPN Darlington Power Transistor**

**2SD1248**

**DESCRIPTION**

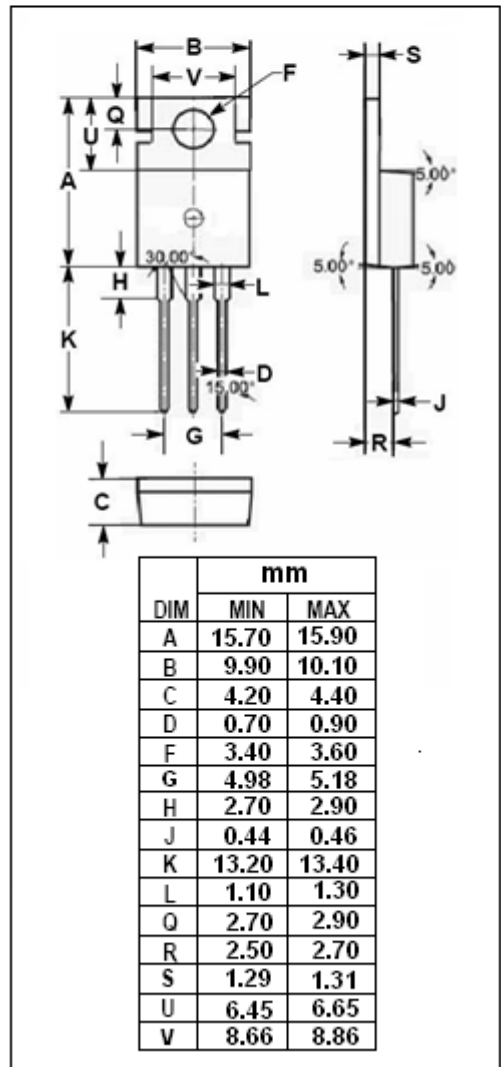
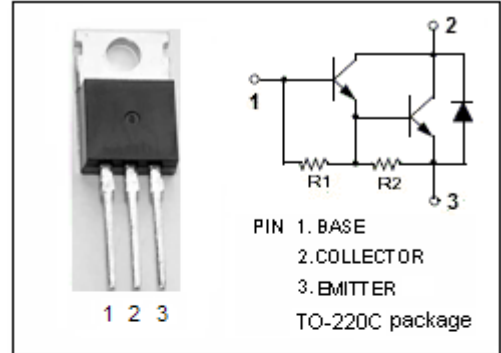
- Collector-Emitter Breakdown Voltage-  
:  $V_{(BR)CEO} = 120V(\text{Min})$
- High DC Current Gain  
:  $h_{FE} = 1000(\text{Min}) @ I_C = 4A$
- Low Collector Saturation Voltage

**APPLICATIONS**

- Designed for low frequency power amplifiers applications.

**ABSOLUTE MAXIMUM RATINGS( $T_a = 25^\circ\text{C}$ )**

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	120	V
$V_{CEO}$	Collector-Emitter Voltage	120	V
$V_{EBO}$	Emitter-Base Voltage	7	V
$I_C$	Collector Current-Continuous	8	A
$I_{CP}$	Collector Current-Peak	12	A
$P_C$	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	40	W
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{stg}$	Storage Temperature Range	-55~150	$^\circ\text{C}$



**isc Silicon NPN Darlington Power Transistor****2SD1248****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C= 25\text{mA}; R_{BE}= \infty$	120			V
$V_{(BR)EBO}$	Emitter -Base Breakdown Voltage	$I_E= 100\text{mA}; I_C= 0$	7			V
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C= 4\text{A}; I_B= 8\text{mA}$			1.5	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C= 8\text{A}; I_B= 80\text{mA}$			3.0	V
$V_{BE(sat)-1}$	Base-Emitter Saturation Voltage	$I_C= 4\text{A}; I_B= 8\text{mA}$			2.0	V
$V_{BE(sat)-2}$	Base-Emitter Saturation Voltage	$I_C= 8\text{A}; I_B= 80\text{mA}$			3.5	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB}= 120\text{V}; I_E= 0$			100	$\mu\text{A}$
$I_{CEO}$	Collector Cutoff Current	$V_{CE}= 100\text{V}; R_{BE}= \infty$			10	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C= 4\text{A}; V_{CE}= 3\text{V}$	1000		20000	
$V_{ECF}$	C-E Diode Forward Voltage	$I_F= 8\text{A}$			3.0	V